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- Drives up to 20 Lines
- 70-V Output Voltage Swing Capability
- 40-mA Output Source Current Capability
- High-Speed Serially-Shifted Data Input
- CMOS-Compatible Inputs
- Direct Replacement for Sprague UCN5812A

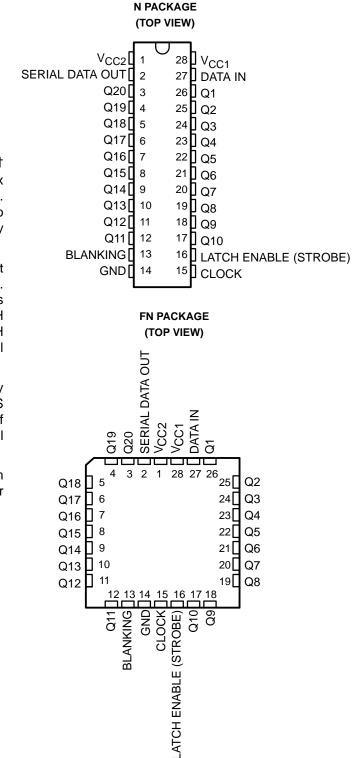
description

The TL5812 and TL5812I are monolithic BIDFET[†] integrated circuits designed to drive a dot matrix or segmented vacuum fluorescent display (VFD). Each device features a serial data output to cascade additional devices for large display arrays.

A 20-bit data word is serially loaded into the shift register on the low-to-high transition of CLOCK. Parallel data is transferred to the output buffers through a 20-bit D-type latch while LATCH ENABLE is high and is latched when LATCH ENABLE is low. When BLANKING is high, all outputs are low.

The outputs are totem-pole structures formed by npn emitter-follower and double-diffused MOS (DMOS) transistors with output voltage ratings of 70 V and a source-current capability of 40 mA. All inputs are CMOS compatible.

The TL5812 is characterized for operation from 0° C to 70°C. The TL5812I is characterized for operation from -40° C to 85°C.



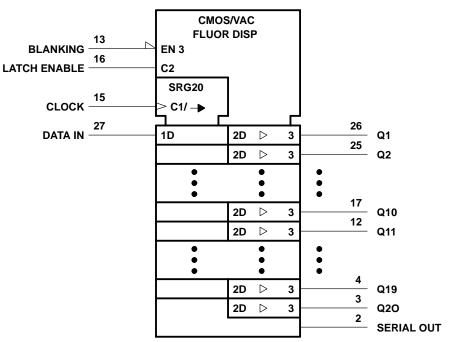
†BIDFET – Bipolar, double-diffused, N-channel and P-channel MOS transistors on same chip. This is a patented process.



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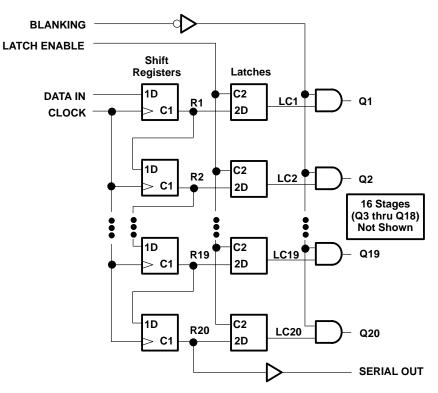
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logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





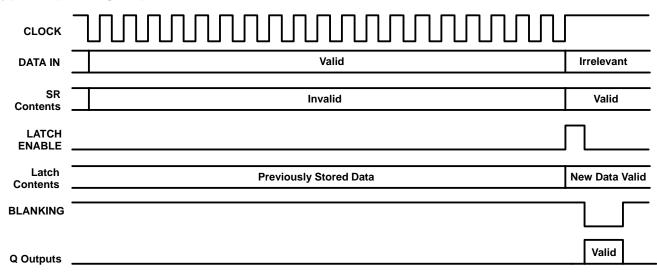
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	FUNCTION TABLE									
FUNCTION	CONTROL INPUTS		SHIFT REGISTERS	LATCHES	OUTPUTS					
	CLOCK	LATCH ENABLE	BLANKING	R1 THRU R20	LC1 THRU LC20	SERIAL	Q1 THRU Q20			
Load	↑ No↑	X X	X X	Load and shift [†] No change	Determined by LATCH ENABLE [‡]	R20 R20	Determined by BLANKING			
Latch	X X	L H	X X	As determined above	Stored data New data	R20 R20	Determined by BLANKING			
Blank	X X	X X	H L	As determined above	Determined by LATCH ENABLE [‡]	R20 R20	All L LC1 thru LC10, respectively			

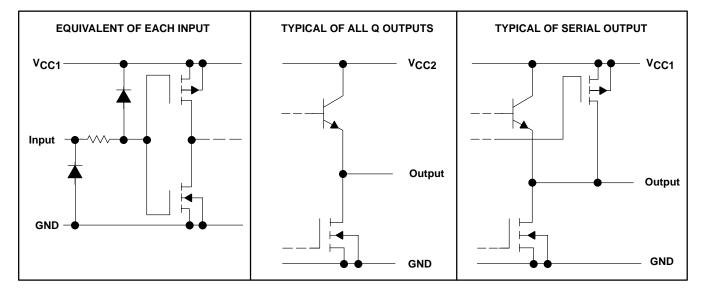
 $H = high \ level, \qquad L = low \ level, \qquad X = irrelevant, \qquad \uparrow = low-to-high-level \ transition.$

R20 takes on the state of R19, R19 takes on the state of R18, ... R2 takes on the state of R1, and R1 takes on the state of the data input.
New data enter the latches while LATCH ENABLE is high. These data are stored while LATCH ENABLE is low.

typical operating sequence



schematics of inputs and outputs





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

$\begin{array}{llllllllllllllllllllllllllllllllllll$	
Operating free-air temperature range: TL5812	
Storage temperature range, Case temperature for 10 seconds: FN package Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	65°C to 150°C

NOTE 1: All voltage values are with respect to GND.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
FN	1400 mW	11.2 mW/°C	896 mW	728 mW
Ν	1150 mW	9.2 mW/°C	736 mW	598 mW

recommended operating conditions

		MIN N	OM MAX	UNIT	
Supply voltage, V _{CC1}	4.5	15	V		
Supply voltage, V _{CC2}		0	60	V	
High-level input voltage, VIH		V _{CC1} -1.5	V _{CC1} +0.3	V	
Low-level input voltage, VIL	-0.3†	0.8	V		
High-level output current, IOH			-40) mV	
Operating free air temperature. Te	TL5812	0	70	°C	
Operating free-air temperature, T _A	TL5812I	-40	85	J	

[†] The algebraic convention, in which the less positive (more negative) limit is designated as minimum, is used in this data sheet for logic voltage levels.



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electrical characteristics over operating free-air temperature range, $V_{DD} = 5$ V to 15 V, $V_{BB} = 60$ V (unless otherwise noted)

	PARAMETER			TEST CONDITIONS			MAX	UNIT
	High-level output	Q outputs	I _{OH} = -25 mA		57.5	58.2		
∨он		SERIAL DATA OUT	V _{CC1} = 5 V,	I _{OH} = -20 μA	4.5	4.9		V
		SERIAL DATA OUT	V _{CC1} = 15 V,	I _{OH} = -20 μA	14.5	14.9		
		Q outputs	I _{OL} = 1 mA,	BLANKING at V _{CC1}		0.7	1.5	V
VOL Low-level out	Low-level output voltage	SERIAL DATA OUT	V _{CC1} = 5 V,	I _{OL} = 20 μA		0.06	0.3	
		SERIAL DATA OUT	V _{CC1} = 15 V,	I _{OL} = 20 μA		0.03	0.3	
Ιн	High-level input current	$V_I = V_{CC1}$			0.3	1	μΑ	
ЧL	L Low-level input current					-0.3	-1	μA
I _{OL}	OL Low-level output current (pulldown current)			BLANKING at V _{CC1}	2.5	3.2		μΑ
IO(off)	Off-state output current		V _O = 0,	BLANKING at V _{CC1}		< - 1	-15	μA
		Cumply current frame \/				3.5	8	mA
ICC2	Supply current from V _{CC2}		Outputs low			0.02	0.5	mA
			V _{CC1} = 5 V			1.5	3	mA
ICC1	Supply current from VCC1		V _{CC1} = 15 V			1.7	4	ША

[‡] All typical characteristics are at T_A = 25°C.

timing requirements over operating free-air temperature range

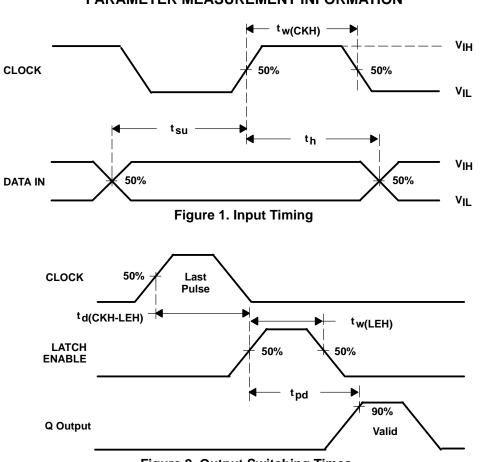
			MIN	MAX	UNIT	
^t w(CKH)	Pulse duration, CLOCK high	V _{CC1} = 5 V	500		ns	
		V _{CC1} = 15 V	100		115	
+ 4 = 10	Pulse duration, LATCH ENABLE high	V _{CC1} = 5 V	500		ns	
^t w(LEH)		V _{CC1} = 15 V	100			
.	Setup time, DATA IN before CLOCK [↑]	V _{CC1} = 5 V	150		ns	
^t su(D)		V _{CC1} = 15 V	75		115	
^t h(D)	Hold time, DATA IN after CLOCK \uparrow	V _{CC1} = 5 V	150		ns	
		V _{CC1} = 15 V	75		115	
^t d(CKH-LEH)	Delay time, CLOCK↑ to LATCH ENABLE high	V _{CC1} = 5 V	150		ns	
	beidy time, decore to externe inside high	V _{CC1} = 15 V	75		115	

switching characteristics, V_{BB} = 60 V, T_A = 25°C

	PARAMETER			TYP	MAX	UNIT
		V _{CC1} = 5 V		2.2		
۲pd	Propagation delay time, LATCH ENABLE to Q outputs	V _{CC1} = 15 V		0.8		μs



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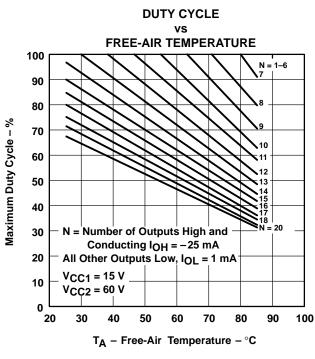


Figure 3



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